



### General Description

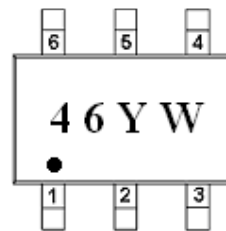
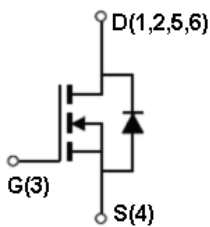
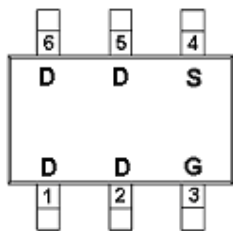
AFN3446, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- 20V/4.0A,  $R_{DS(ON)}=58m\Omega@V_{GS}=4.5V$
- 20V/3.6A,  $R_{DS(ON)}=68m\Omega@V_{GS}=2.5V$
- 20V/3.0A,  $R_{DS(ON)}=88m\Omega@V_{GS}=1.8V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TSOP-6 package design

### Pin Description ( TSOP-6 )



### Application

- Portable Equipment
- Battery Powered System
- Net Working System

### Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN3446TS6RG	46YW	TSOP-6	Tape & Reel	3000 EA

- ※ 46 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFN3446TS6RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



## Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	4.0
		T <sub>A</sub> =70°C	3.0
Pulsed Drain Current	I <sub>DM</sub>	20	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1.6	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2.0
		T <sub>A</sub> =70°C	1.3
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

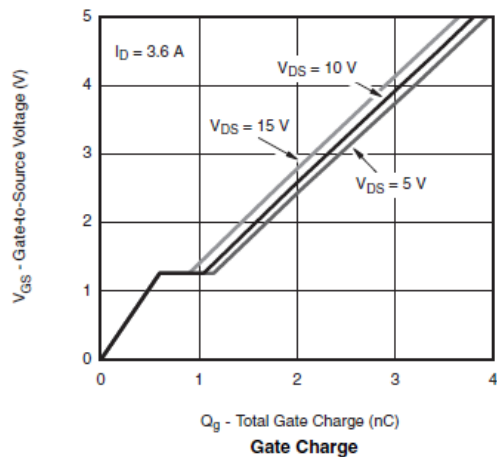
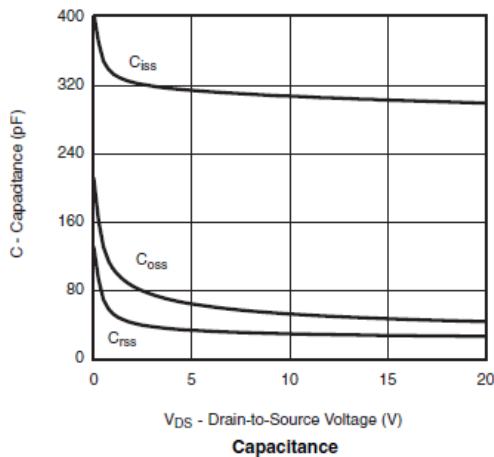
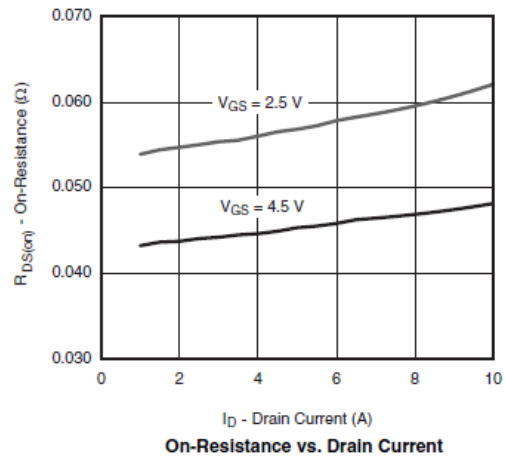
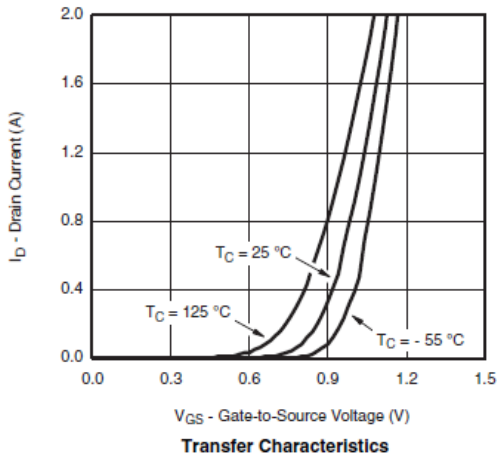
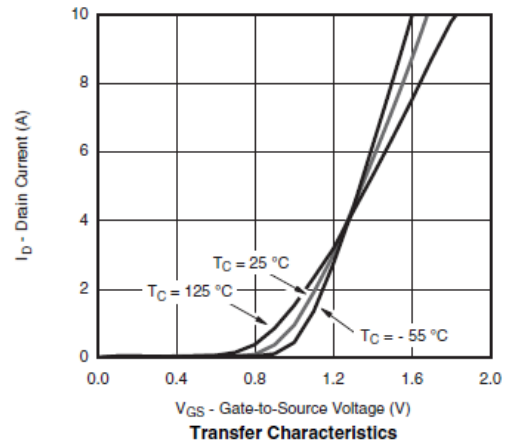
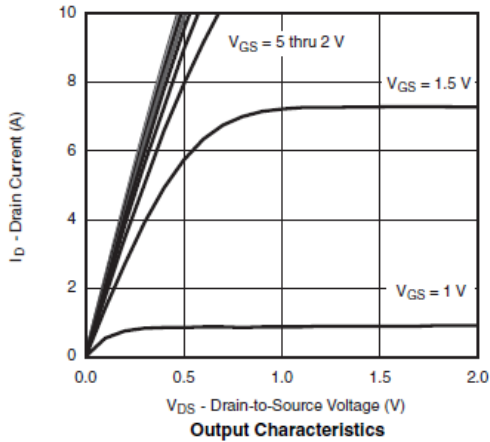
## Electrical Characteristics

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.3		0.8	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =16V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			10	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =4.5V	6			A
		V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =2.5V	4			
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.0A		46	58	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.6A		56	68	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =3.0A		72	88	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =3.6A		10		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.6A, V <sub>GS</sub> =0V		0.85	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V I <sub>D</sub> ≧3.6A		4.2	5.0	nC
Gate-Source Charge	Q <sub>gs</sub>			0.6		
Gate-Drain Charge	Q <sub>gd</sub>			0.4		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V f=1MHz		340		pF
Output Capacitance	C <sub>oss</sub>			115		
Reverse Transfer Capacitance	C <sub>rss</sub>			33		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, R <sub>L</sub> =2.8Ω I <sub>D</sub> ≧3.6A, V <sub>GEN</sub> =4.5V R <sub>G</sub> =1Ω		8	15	ns
	t <sub>r</sub>			8	15	
Turn-Off Time	t <sub>d(off)</sub>			25	40	
	t <sub>f</sub>			8	15	

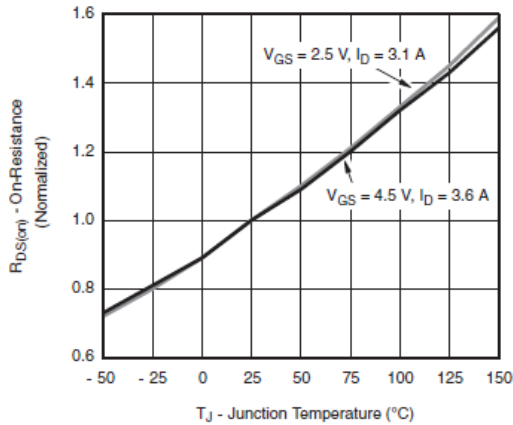


## Typical Characteristics

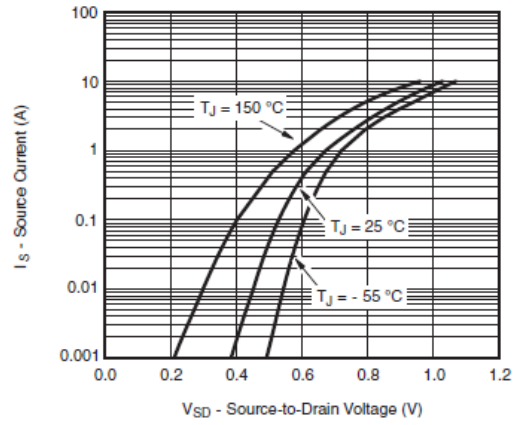




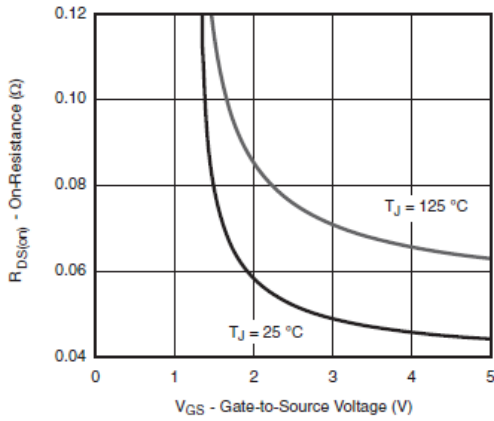
## Typical Characteristics



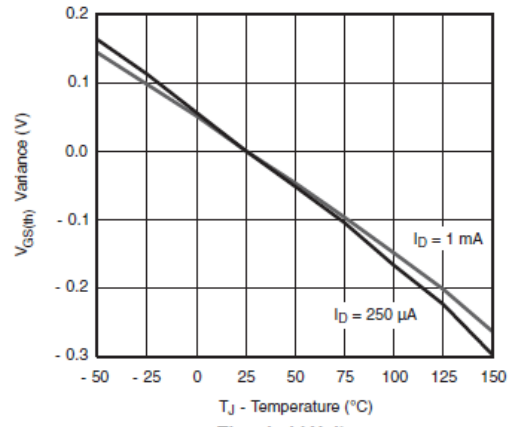
On-Resistance vs. Junction Temperature



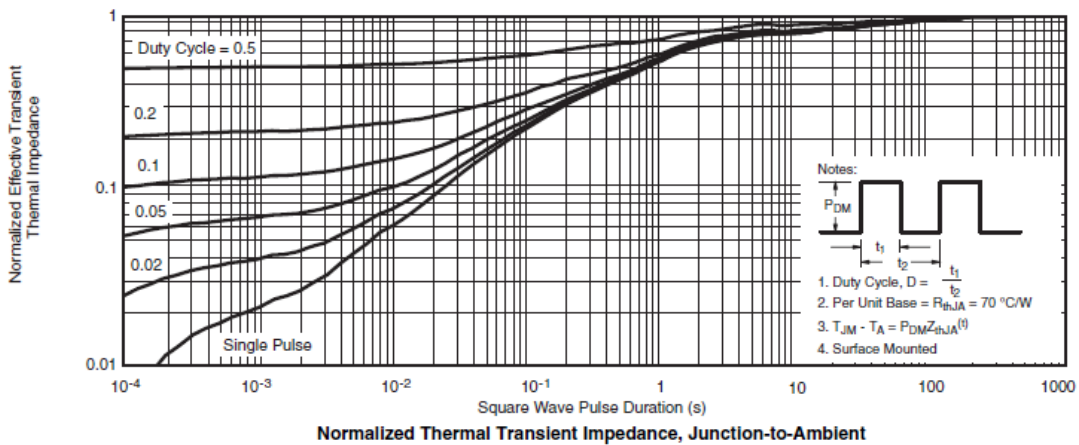
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

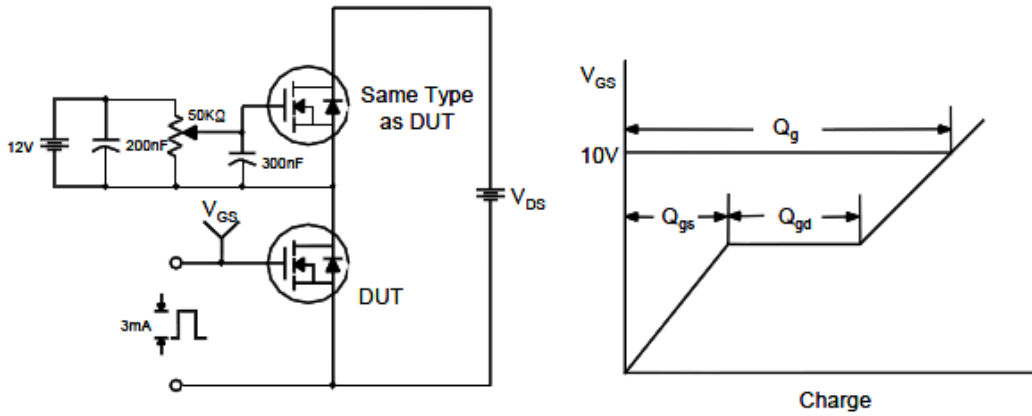


Normalized Thermal Transient Impedance, Junction-to-Ambient

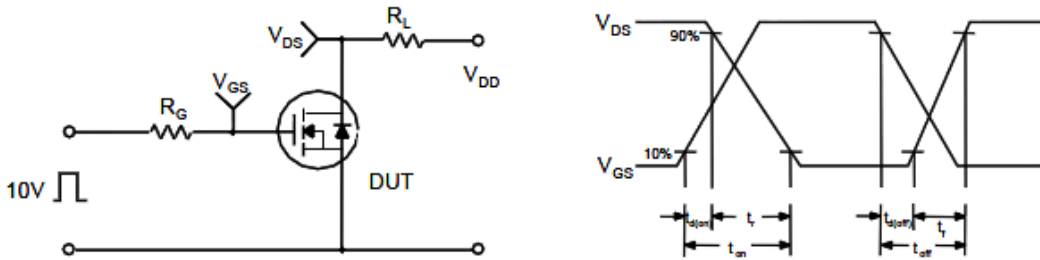


## Typical Characteristics

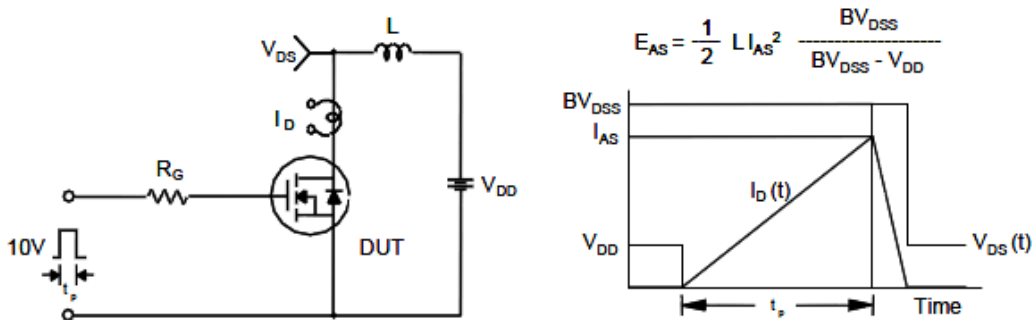
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

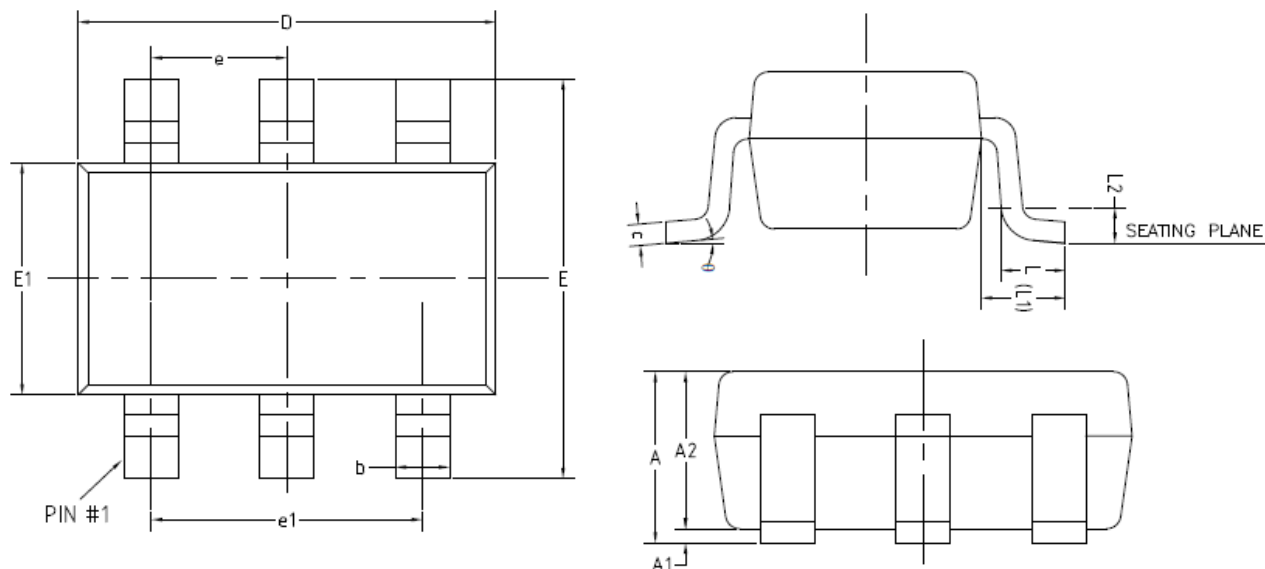


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( TSOP-6 )**



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	—	0.90
A1	0	—	0.10
A2	0.70	0.75	0.80
b	0.35	—	0.50
c	0.08	—	0.20
D	2.82	2.92	3.02
E	2.65	2.80	2.95
E1	1.60	1.65	1.70
e	0.95(BSC)		
e1	1.90(BSC)		
L	0.30	0.45	0.60
L1	0.59REF		
L2	0.25BSC		
θ	0°	—	8°

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